

**Abstract of the Disclosure**

An n-type layer of the opposite conduction type composed of n-GaN is formed between a light emitting layer and a p-type cladding layer composed of p-AlGaN. The bandgap of the n-type 5 layer of the opposite conduction type is larger than the bandgap of the light emitting layer and is smaller than the bandgap of the p-type cladding layer.